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				Application Number	10/510,916
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				Art Unit	1795
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Sheet	1	of	1	Attorney Docket Number	Q84137

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
		M. TAKAHASHI, et al.: "Tantalum nitride films for the absorber material of reflective-type EUVL mask", Proceedings of the Spie, The International Society for Optical Engineering Spie-Int. Soc. Opt. Eng USA, 2001, pages 760-770, Vol. 4343.	
		SHINJI TSUBOI, et al., Recent progress in 1Xx-ray mask technology: Feasibility Study using ASET-NIST format TaXN x-ray masks with 100 nm rule 4 Gbit dynamic random access memory test patterns, 2001 American Society, pgs. 2416-2422.	
		KENNETH RACETTE, et al., Sputter deposition and annealing of Ta, TaSi <sub>x</sub> and TaB <sub>x</sub> composite films and their application in next generation lithography masks, 2000 American Vacuum Society, pgs. 1119-1124.	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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